

<b>FORM PTO-1449</b> US DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE  If AFTER the later date of the first Office Action or 3 months from filing, use only with Rule 97(E) Certificate or Fee  <b>LIST OF ART CITED BY APPLICANT</b> <i>(Use several sheets if necessary)</i>		Atty. Docket No. <b>80236AJDL</b>		Serial No. <b>09-526286</b> <del>To Be Assigned</del>	
		Applicant: <b>Ramanathan Srinivasan, et al</b>			
		Filing Date <b>Herewith</b>		Group <b>1763</b> <del>To Be Assigned</del>	

  

U.S. PATENT DOCUMENTS						
Examiner Initial*	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPR.
<i>gag</i>	5,738,800	14Apr1998	Hosali et al.	216	99	
<i>gag</i>	5,759,917	02Jun1998	Grover et al.	438	690	

  

FOREIGN PATENT DOCUMENTS						
Examiner Initial*	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	FILING DATE IF APPR.
<i>gag</i>	0 786 504 A2	30Jul1997	EP	<del>Q</del>	<del>102</del>	<del>Q</del>
	0 846 740 A1	10Jun1998	EP	<del>Q</del>	<del>102</del>	<del>Q</del>
<i>gag</i>	0 853 335 A2	15Jul1998	EP	<del>Q</del>	<del>216505</del>	<del>Q</del>

  

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)	
<i>gag</i>	Chemical Mechanical Planarization of Microelectronic Materials, "8.1.2 Shallow Trench Isolation"; by J. M. Steigerwald, S. P. Muraka, and R. J. Gutman; ISBN 0-471-13827-4 (Jon Wiley & Son, Inc. 1997), pages 273-274.
	A High Oxide:Nitride Selectivity CMP Slurry For Shallow Trench Isolation; by Sharath Hosali and Ray Lavoie; Electrochemical Society Proceedings, Volume 98-7, pages 218-234.
	Application of Ceria-Based High Selectivity Slurry to STI CMP for Sub 0.18 $\mu$ m CMOS Technologies; by Ki-Sik Choi, Sang-Ick Lee, Chang-Il Kim, Chul-Woo Nam, Sam-Dong Kim, and Chung-Tae Kim; CMP-MIC Conference, February 11-12, 1999, pages 307-313.
	A Production-Proven Shallow Trench Isolation (STI) Solution Using Novel CMP Concepts; by Raymond R. Jin, Jeffery David, Bob Abbassi, Tom Osterheld, and Fritz Redeker; CMP-MIC Conference, February 11-12, 1999, pages 314-321.
	A Wide Margin CMP and Clean Process For Shallow Trench Isolation Applications; by Brad Withers, Eugene Zhao, Rahul Jairath; CMP-MIC Conference, February 19-20, 1998, pages 319-327.
	Planarization Process and Consumable Development For Shallow Trench Isolation; by Sharath D. Hosali, et al.; CMP-MIC Conference, February 13-14, 1997, pages 52-57.
	Pattern Dependence And Planarization Using Silica Or Ceria Slurries For Shallow Trench Isolation; by D. R. Evans, et al.; CMP-MIC Conference, February 19-20, 1998, pages 347-350.
	A Two-Step CMP-RIE Planarization Sequence For Advanced Trench Isolation Process; by Konstantin Smekalin; CMP-MIC Conference, February 13-14, 1997, pages 21-28.
<i>gag</i>	Raising Oxide:Nitride Selectivity To Aid In The CMP Of Shallow Trench Isolation Type Applications; by C.R. Mills, et al.; CMP-MIC Conference, February 13-14, 1997, pages 179-185.

  

EXAMINER <i>George Gould reave</i>	DATE CONSIDERED <b>11-01</b>
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\*EXAMINER: Initial if reference considered whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.